

RF POWER TRANSISTOR

DESCRIPTION:

The **ASI AM0912-150** is a Common Base Transistor Designed for TCAS and JTIDS Pulse Power Amplifier Applications.

FEATURES INCLUDE:

- Gold Metallization
- Hermetic Package
- Input/Output Matching

MAXIMUM RATINGS

| | |
|-------------------------|-----------------------------------|
| I_C | 16.5 A |
| V_{CC} | 35 V |
| P_{DISS} | 300 W @ T _C = ≤ 100 °C |
| T_J | -65 °C to +250 °C |
| T_{STG} | -65 °C to +200 °C |
| θ_{JC} | 0.57 °C/W |

PACKAGE - .400 X .500 2L FLG

| | MINIMUM INCHES/MM | MAXIMUM INCHES/MM | | MINIMUM INCHES/MM | MAXIMUM INCHES/MM |
|---|-------------------|-------------------|---|-------------------|-------------------|
| A | .140/3.56 | | J | .750/19.75 | |
| B | .110/2.80 | | K | .386/9.80 | |
| C | .110/2.80 | | L | .900/22.86 | |
| D | .395/10.03 | .407/10.34 | M | .120/3.05 | |
| E | .193/4.90 | | N | .900/22.70 | |
| F | | .230/5.84 | O | .050/1.27 | |
| G | .005/0.06 | .006/0.15 | P | | .170/4.32 |
| H | .118/3.00 | .151/3.83 | Q | .062/1.58 | |
| I | | .083/2.10 | | | |

CHARACTERISTICS T_C = 25 °C

| SYMBOL | TEST CONDITIONS | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|-------------------------|---|---------|---------|---------|-------|
| BV_{CBO} | I _C = 60 mA | 55 | | | V |
| BV_{CES} | I _C = 100 mA | 55 | | | V |
| BV_{EBO} | I _E = 10 mA | 3.5 | | | V |
| I_{CES} | V _{CB} = 35 V | | | 25 | mA |
| h_{FE} | V _{CE} = 5.0 V I _C = 5.0 A | 20 | | | --- |
| P_{OUT} | V _{CC} = 35 V f = 960 to 1215 MHz P _{IN} = 26.7 W | 300 | 330 | | W |
| P_G | | 7.0 | 7.4 | | dB |
| η_C | | 38 | 45 | | % |